

N-Channel 150-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
150	0.021 at $V_{GS} = 10$ V	85

FEATURES

- TrenchFET® Power MOSFET
- 175 °C Junction Temperature

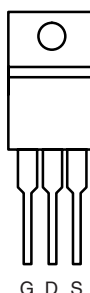
APPLICATIONS

- Primary Side Switch



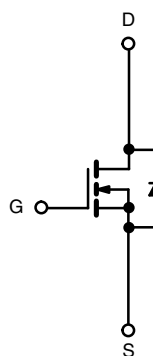
Available
RoHS*
COMPLIANT

TO-220AB



Top View

DRAIN connected to TAB



N-Channel MOSFET

Ordering Information: SUP85N15-21
SUP85N15-21-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175$ °C)	I_D	85	A
		50	
Pulsed Drain Current	I_{DM}	180	
Avalanche Current	I_{AS}	50	mJ
Single Pulse Avalanche Energy ^b	E_{AS}	125	
Maximum Power Dissipation ^b	P_D	300 ^c	W
		2.4	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient-Free Air	R_{thJA}	62.5	°C/W
Junction-to-Case (Drain)	R_{thJC}	0.4	

Notes:

a. Package limited.

b. Duty cycle ≤ 1 %.

c. See SOA curve for voltage derating.

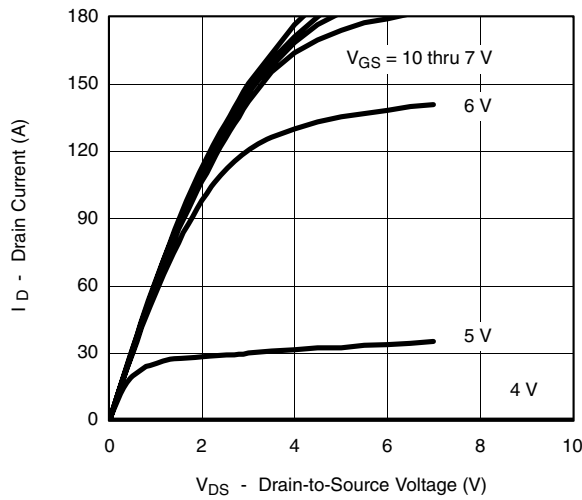
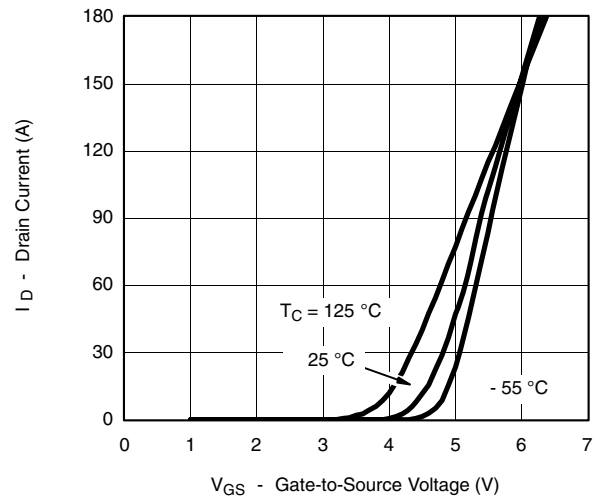
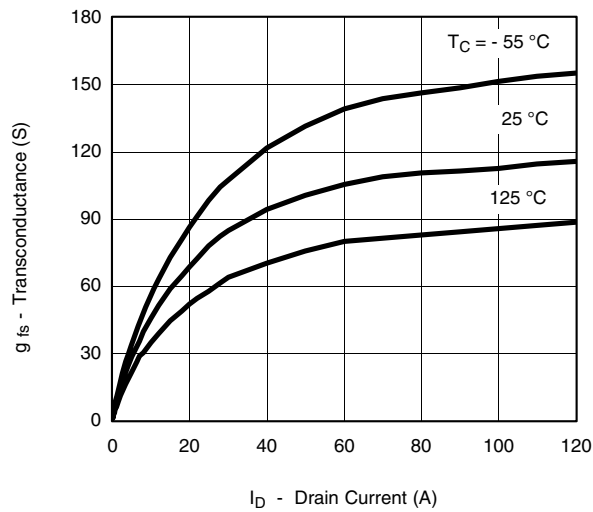
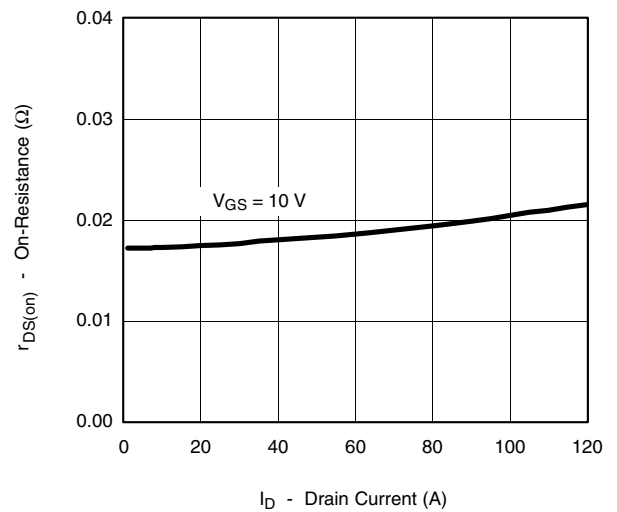
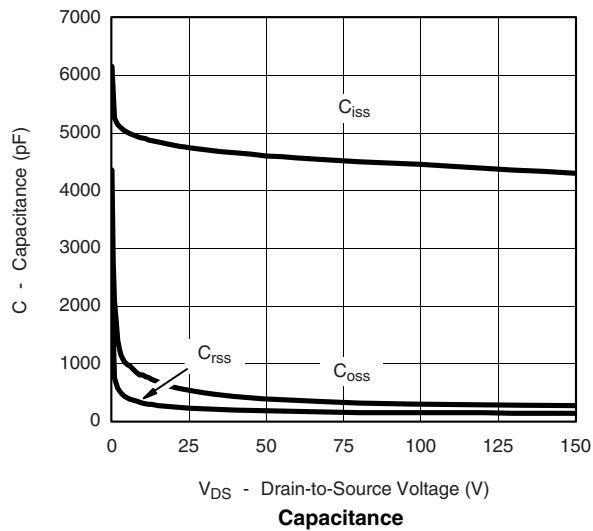
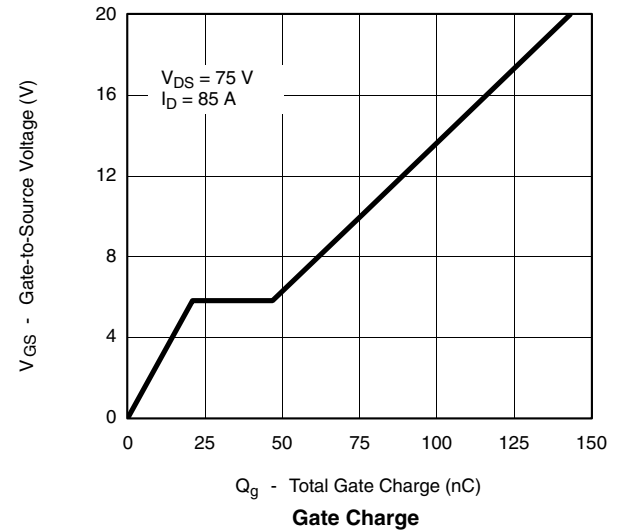
* Pb containing terminations are not RoHS compliant, exemptions may apply.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{DS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	150			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2		4	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 120\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 120\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$			50	
		$V_{DS} = 120\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 175\text{ }^{\circ}\text{C}$			250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$, $V_{GS} = 10\text{ V}$	120			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 30\text{ A}$		0.0175	0.021	Ω
		$V_{GS} = 10\text{ V}$, $I_D = 30\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$			0.042	
		$V_{GS} = 10\text{ V}$, $I_D = 30\text{ A}$, $T_J = 175\text{ }^{\circ}\text{C}$			0.055	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}$, $I_D = 30\text{ A}$	25			S
Dynamic ^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$		4750		pF
Output Capacitance	C_{oss}			530		
Reverse Transfer Capacitance	C_{rss}			220		
Total Gate Charge ^c	Q_g	$V_{DS} = 75\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 85\text{ A}$		76	110	nC
Gate-Source Charge ^c	Q_{gs}			21		
Gate-Drain Charge ^c	Q_{gd}			26		
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 75\text{ V}$, $R_L = 0.9\text{ }\Omega$ $I_D \cong 85\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_G = 2.5\text{ }\Omega$		22	35	ns
Rise Time ^c	t_r			170	250	
Turn-Off Delay Time ^c	$t_{d(off)}$			40	60	
Fall Time ^c	t_f			170	250	
Source-Drain Diode Ratings and Characteristics $(T_C = 25\text{ }^{\circ}\text{C})^b$						
Continuous Current	I_S				85	A
Pulsed Current	I_{SM}				180	
Forward Voltage ^a	V_{SD}	$I_F = 85\text{ A}$, $V_{GS} = 0\text{ V}$		1.0	1.5	V
Reverse Recovery Time	t_{rr}	$I_F = 50\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		130	200	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			8	12	A
Reverse Recovery Charge	Q_{rr}			0.52	1.2	μC

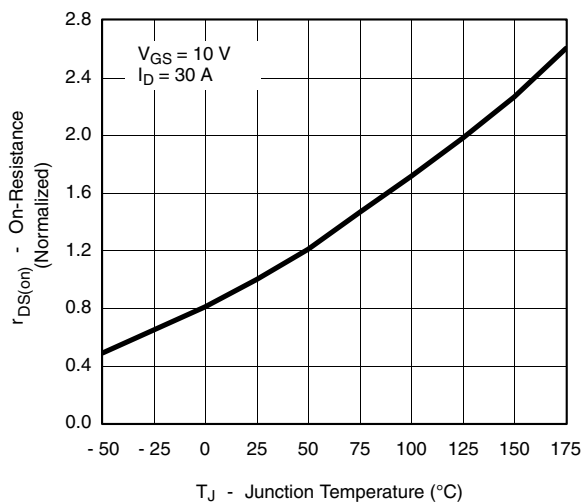
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

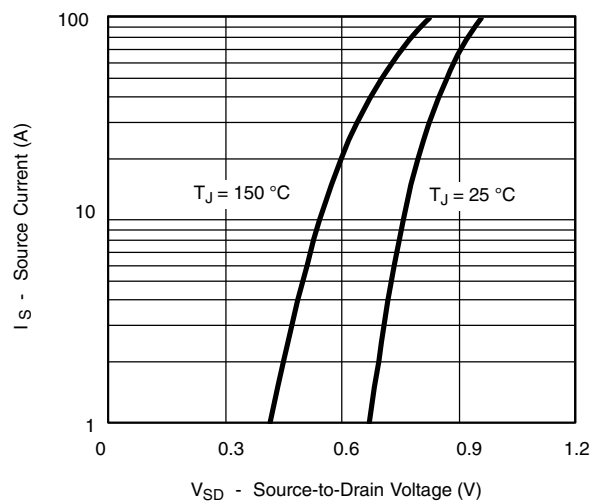
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge

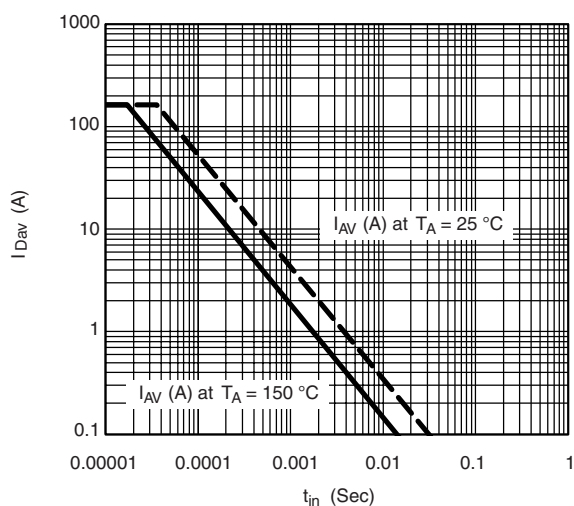
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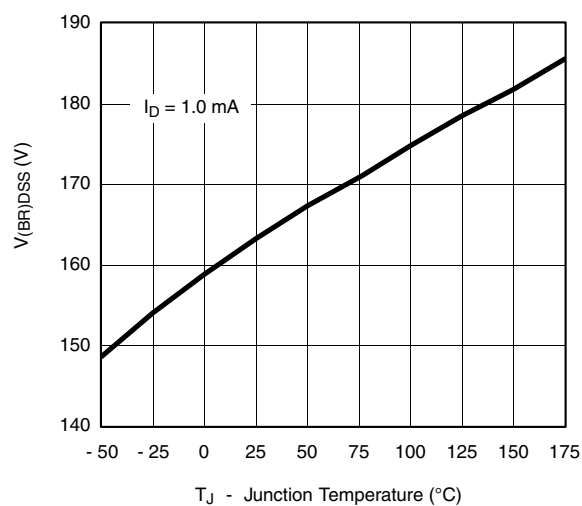
On-Resistance vs. Junction Temperature



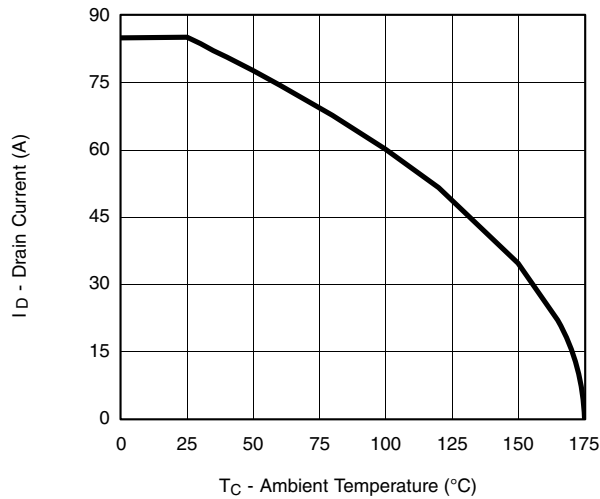
Source-Drain Diode Forward Voltage



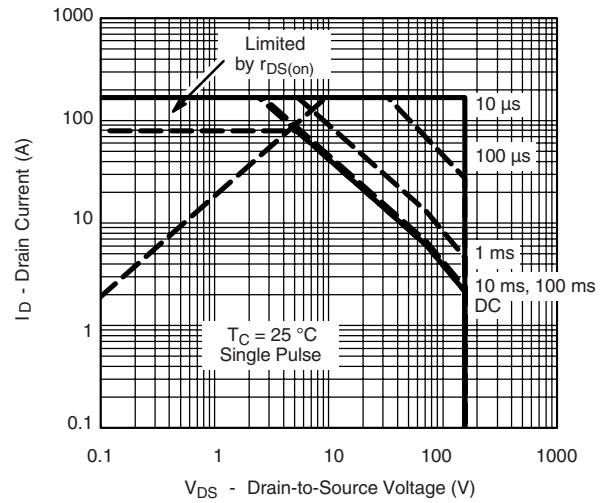
Avalanche Current vs. Time



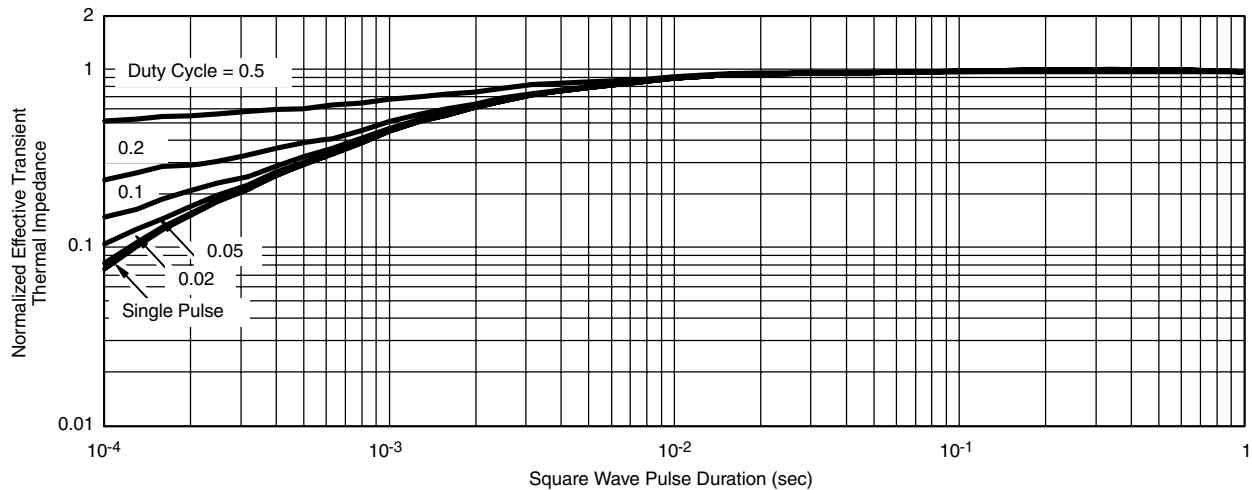
Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS


Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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